Switch-mode Power Rectifier 150 V, 30 A

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capability
- 30 A Total (15 A Per Diode Leg)
- Guard-Ring for Stress Protection
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

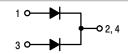
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams (TO-220 & TO-220FP)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



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SCHOTTKY BARRIER RECTIFIER 30 AMPERES, 150 VOLTS



MARKING DIAGRAMS







TO-220 CASE 221A STYLE 6



A = Assembly Location

Y = Year
WW = Work Week
B30H150 = Device Code
G = Pb-Free Device
AKA = Polarity Designator

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

MAXIMUM RATINGS (Per Diode Leg)

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	150	V
Average Rectified Forward Current (Rated V_R) $T_C = 124$ °C	(Per Leg) (Per Device)	I _{F(AV)}	15 30	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase,	60 Hz)	I _{FSM}	200	А
Operating Junction Temperature (Note 1)		TJ	-20 to +150	°C
Storage Temperature		T _{stg}	-65 to +150	°C
Voltage Rate of Change (Rated V _R)		dv/dt	10,000	V/μs
ESD Ratings:	Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating		Symbol	Value	Unit
Maximum Thermal Resistance (MBR30H150CTG)	Junction-to-CaseJunction-to-Ambient	R ₀ JC	2.0 45	°C/W
(MBRF30H150CTG)	- Junction-to-Case	$R_{ hetaJA} \ R_{ hetaJC}$	2.5	

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) $ \begin{array}{l} (I_F=5~A,~T_C=25^\circ C)\\ (I_F=5~A,~T_C=125^\circ C)\\ (I_F=15~A,~T_C=25^\circ C)\\ (I_F=15~A,~T_C=125^\circ C) \end{array} $	VF	0.69 0.55 0.98 0.68	0.75 0.60 1.11 0.73	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, T _C = 25°C) (Rated DC Voltage, T _C = 125°C)	i _R		60 50	μA mA

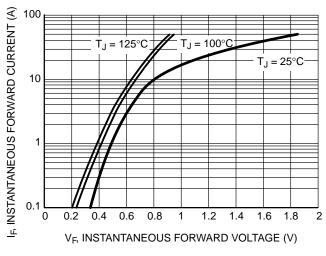
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width = $300 \mu s$, Duty Cycle $\leq 2.0\%$.

DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Shipping [†]
MBRF30H150CTG	TO-220FP (Pb-Free)	50 Units / Rail
MBR30H150CTG	TO-220 (Pb-Free)	50 Units / Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

^{1.} The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.





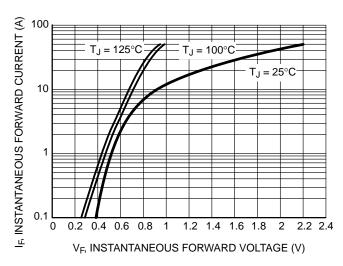


Figure 2. Maximum Forward Voltage

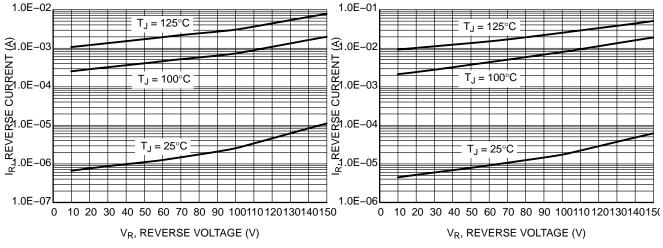


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current

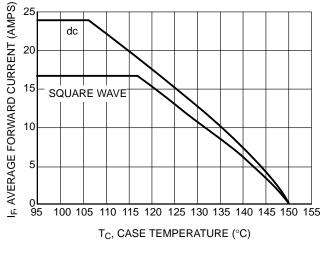


Figure 5. Current Derating

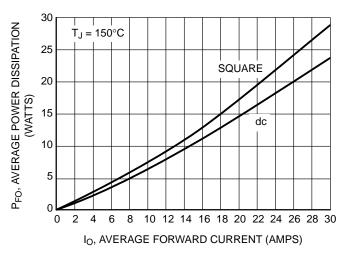


Figure 6. Forward Power Dissipation

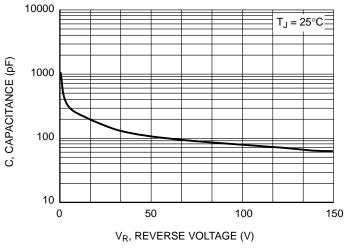


Figure 7. Capacitance

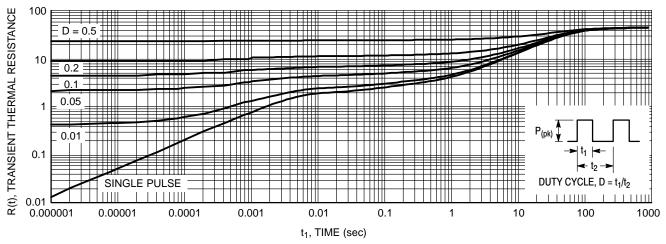


Figure 8. Thermal Response Junction-to-Ambient for MBR30H150CTG

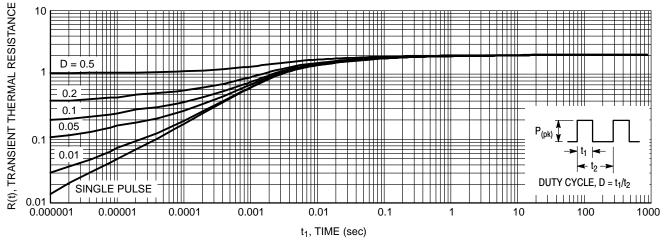


Figure 9. Thermal Response Junction-to-Case for MBR30H150CTG

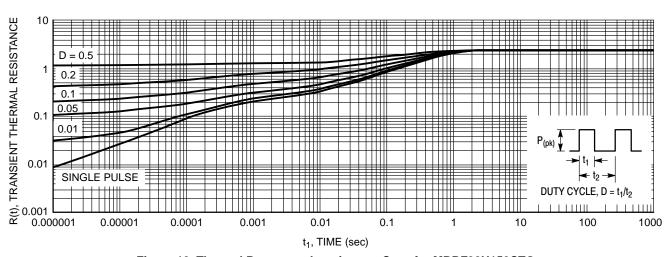
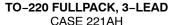
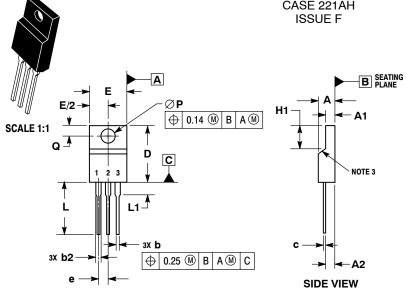


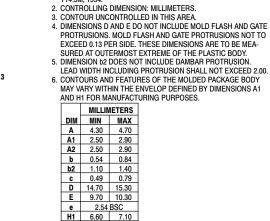
Figure 10. Thermal Response Junction-to-Case for MBRF30H150CTG



CASE 221AH

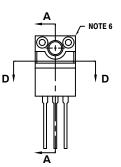
DATE 30 SEP 2014

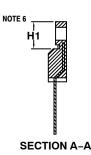




NOTES:







ALTERNATE CONSTRUCTION

GENERIC MARKING DIAGRAM*

2.80 3.00 3.40

4.70

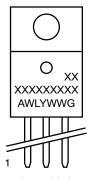
2.90

1.40

0.79

6.60 7.10 12.50 14.73

DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.



= Assembly Location

WL = Wafer Lot = Year

WW = Work Week

G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1:		STYLE 2:	
PIN 1.	MAIN TERMINAL 1	PIN 1.	CATHODE
2.	MAIN TERMINAL 2	2.	ANODE
3.	GATE	3.	GATE

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